

Lecture 11

Digital Circuits (I)

THE INVERTER

Outline

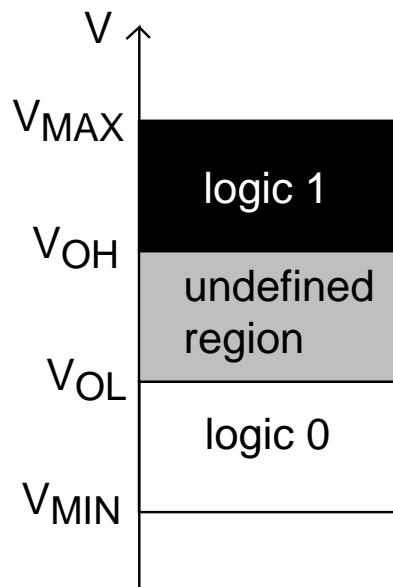
- Introduction to digital circuits
 - The inverter
- NMOS inverter with resistor pull-up

Reading Assignment:

Howe and Sodini; Chapter 5, Sections 5.1-5.3

1. Introduction to digital circuits: the inverter

In digital circuits, digitally-encoded information is represented by means of two distinct voltage ranges:



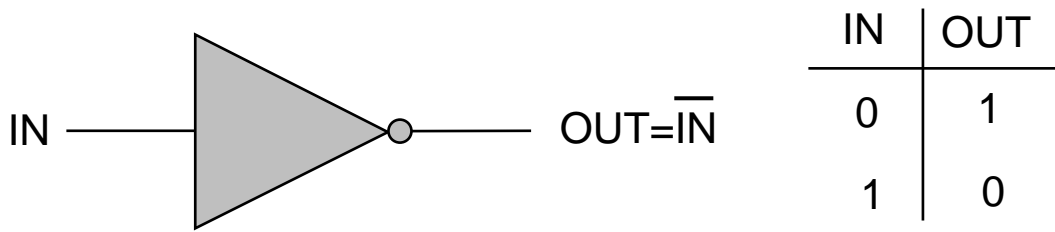
The Static Definition

- **Logic 0:** $V_{MIN} \leq V \leq V_{OL}$
- **Logic 1:** $V_{OH} \leq V \leq V_{MAX}$
- **Undefined logic value:** $V_{OL} \leq V \leq V_{OH}$

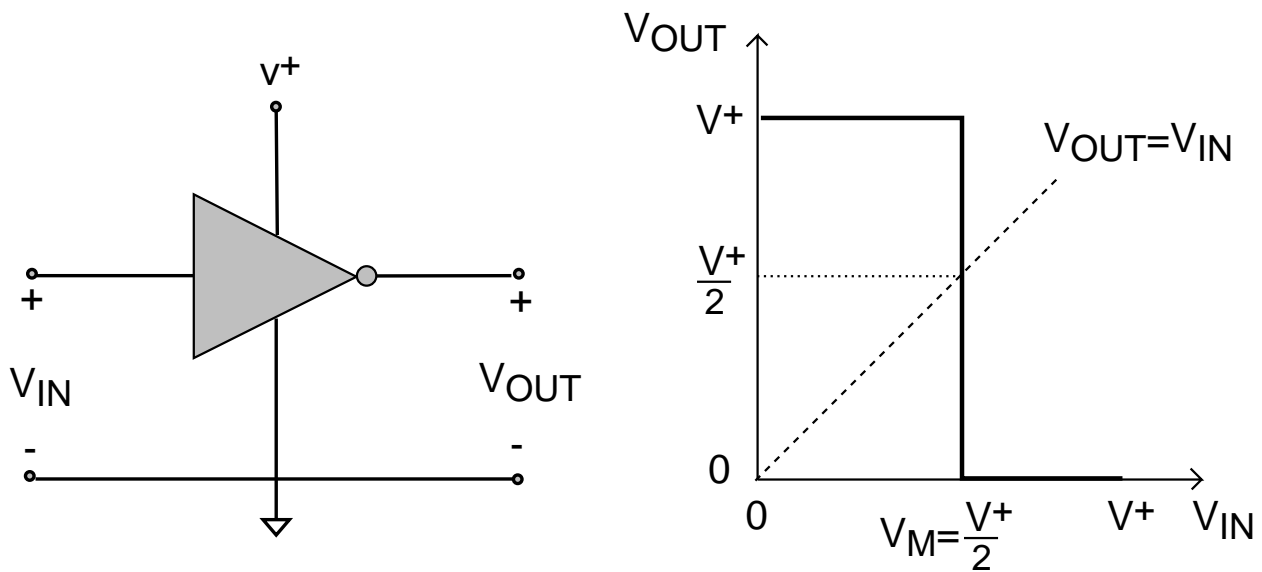
Logic operations are performed using *logic gates*.

Simplest logic operation of all: *inversion* \Rightarrow inverter

Ideal inverter



Circuit representation and ideal transfer function:



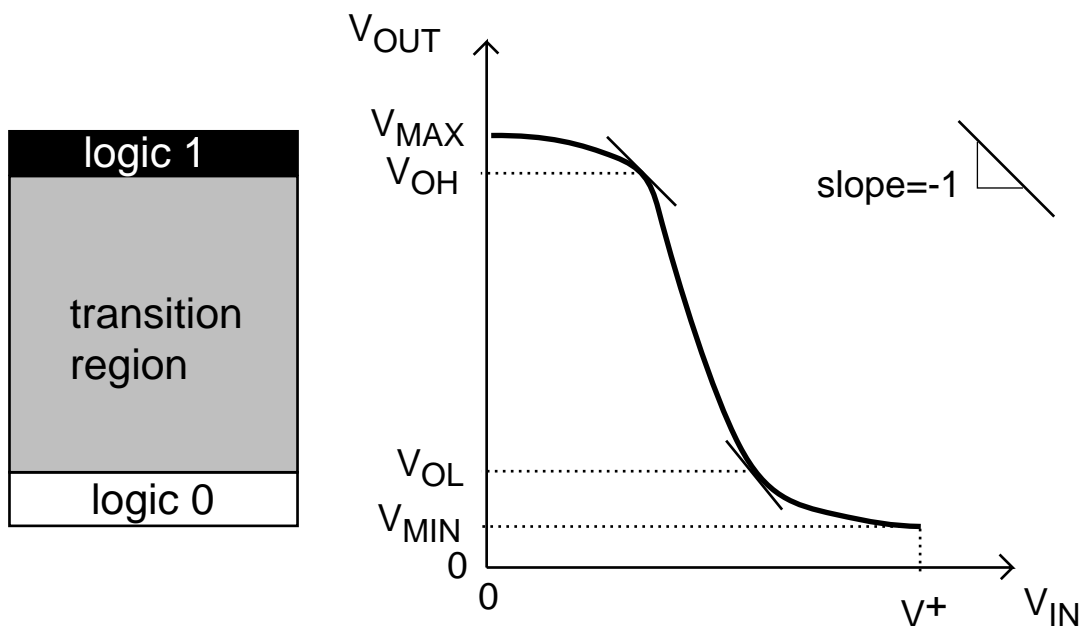
Define *switching point* or *logic threshold* :

- $V_M \equiv$ input voltage for which $V_{OUT} = V_{IN}$
 - For $0 \leq V_{IN} < V_M \Rightarrow V_{OUT} = V^+$
 - For $V_M < V_{IN} \leq V^+ \Rightarrow V_{OUT} = 0$

Ideal inverter returns well defined logical outputs (0 or V^+) even in the presence of considerable noise in V_{IN} (from voltage spikes, crosstalk, etc.)

\Rightarrow signal is *regenerated*!

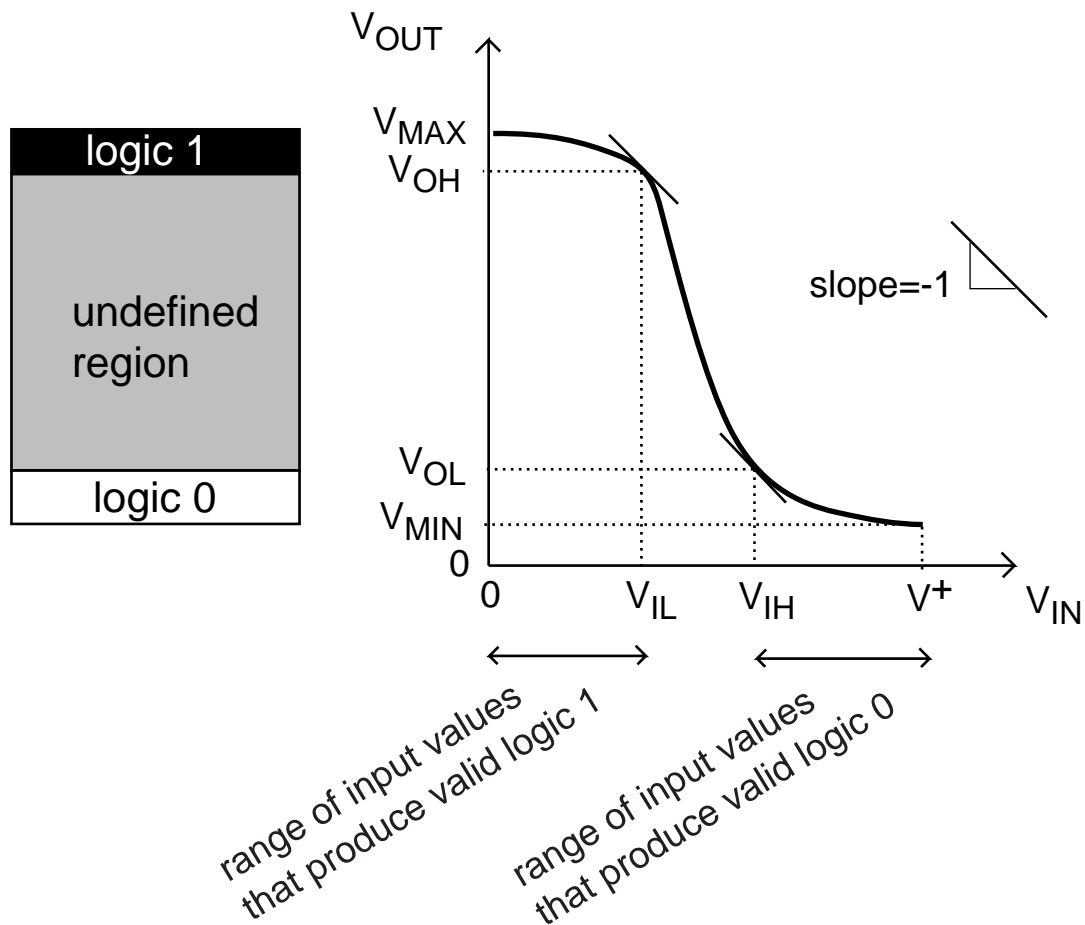
“Real” inverter



In a real inverter, valid logic levels defined as follows:

- Logic 0:
 - $V_{MIN} \equiv$ output voltage for which $V_{IN} = V^+$
 - $V_{OL} \equiv$ smallest output voltage where slope = -1
- Logic 1:
 - $V_{OH} \equiv$ largest output voltage where slope = -1
 - $V_{MAX} \equiv$ output voltage for which $V_{IN} = 0$

Two other important voltages:



Define:

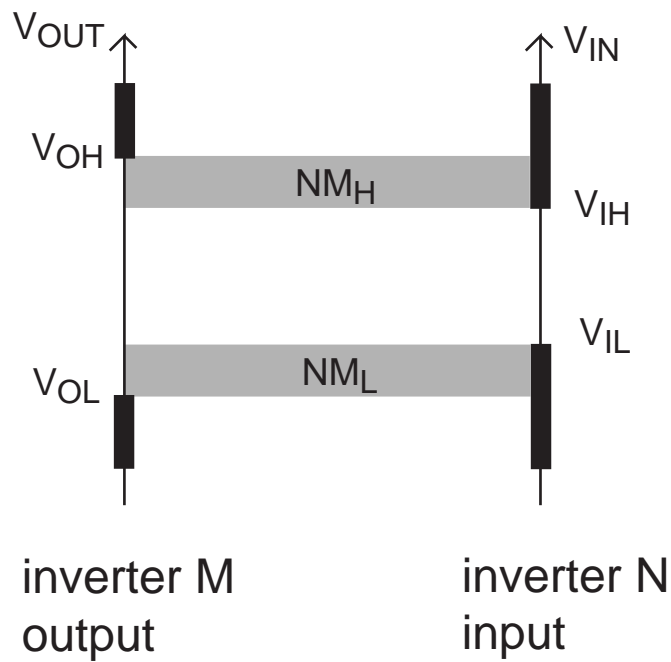
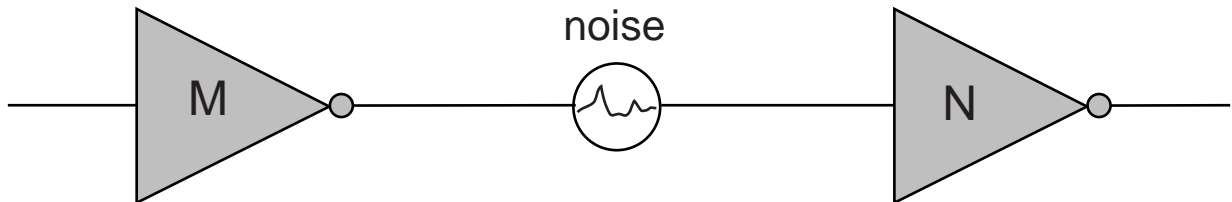
$V_{IL} \equiv$ smallest input voltage where slope = -1

$V_{IH} \equiv$ highest input voltage where slope = -1

If range of output values V_{OL} to V_{OH} is *wider* than the range of input values V_{IL} to V_{IH} , then the inverter exhibits some noise immunity. ($|\text{Voltage gain}| > 1$)

Quantify this through *noise margins*.

Chain of two inverters:



Define *noise margins*:

$$NM_H \equiv V_{OH} - V_{IH}$$

$$NM_L \equiv V_{IL} - V_{OL}$$

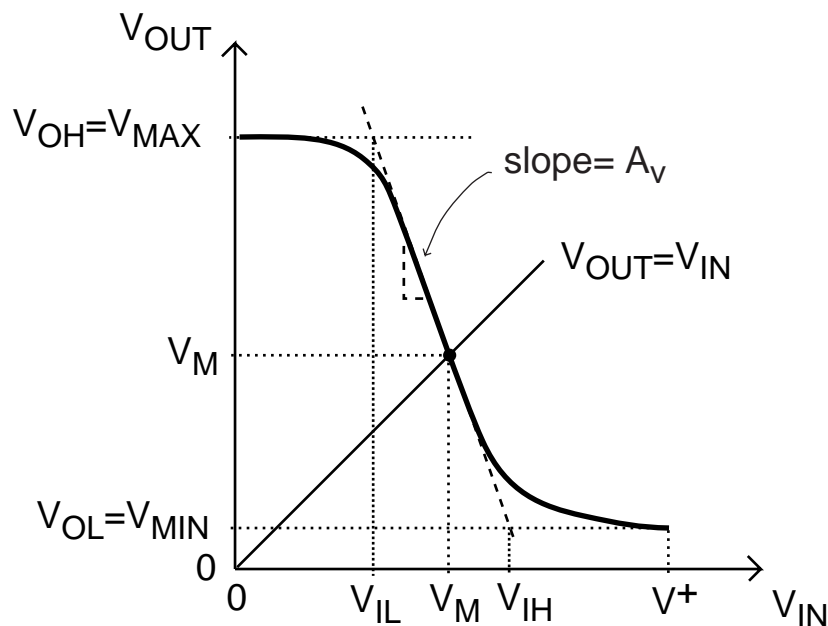
noise margin high

noise margin low

Simplifications for hand calculations: Logic levels and noise margins

It is hard to compute points in transfer function with slope = -1.

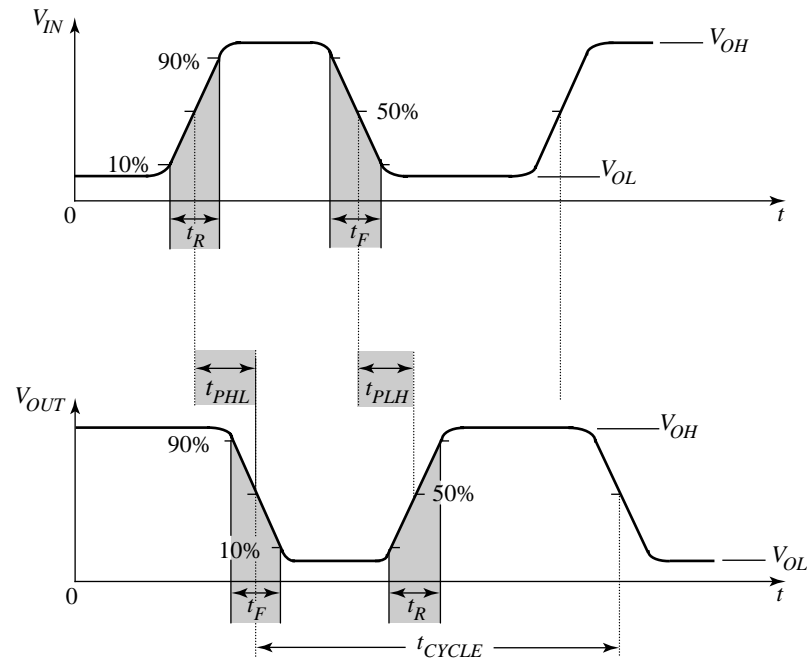
Approximate in the following way:



- Assume $V_{OL} \approx V_{MIN}$ and $V_{OH} \approx V_{MAX}$
- Trace tangent of transfer function at V_M
 - Slope = small signal voltage gain (A_v) at V_M
- $V_{IL} \approx$ intersection of tangent with $V_{OUT} = V_{MAX}$
- $V_{IH} \approx$ intersection of tangent with $V_{OUT} = V_{MIN}$

Transient Characteristics

Inverter switching in the time domain:



t_R \equiv *rise time* between 10% and 90% of total swing

t_F \equiv *fall time* between 90% and 10% of total swing

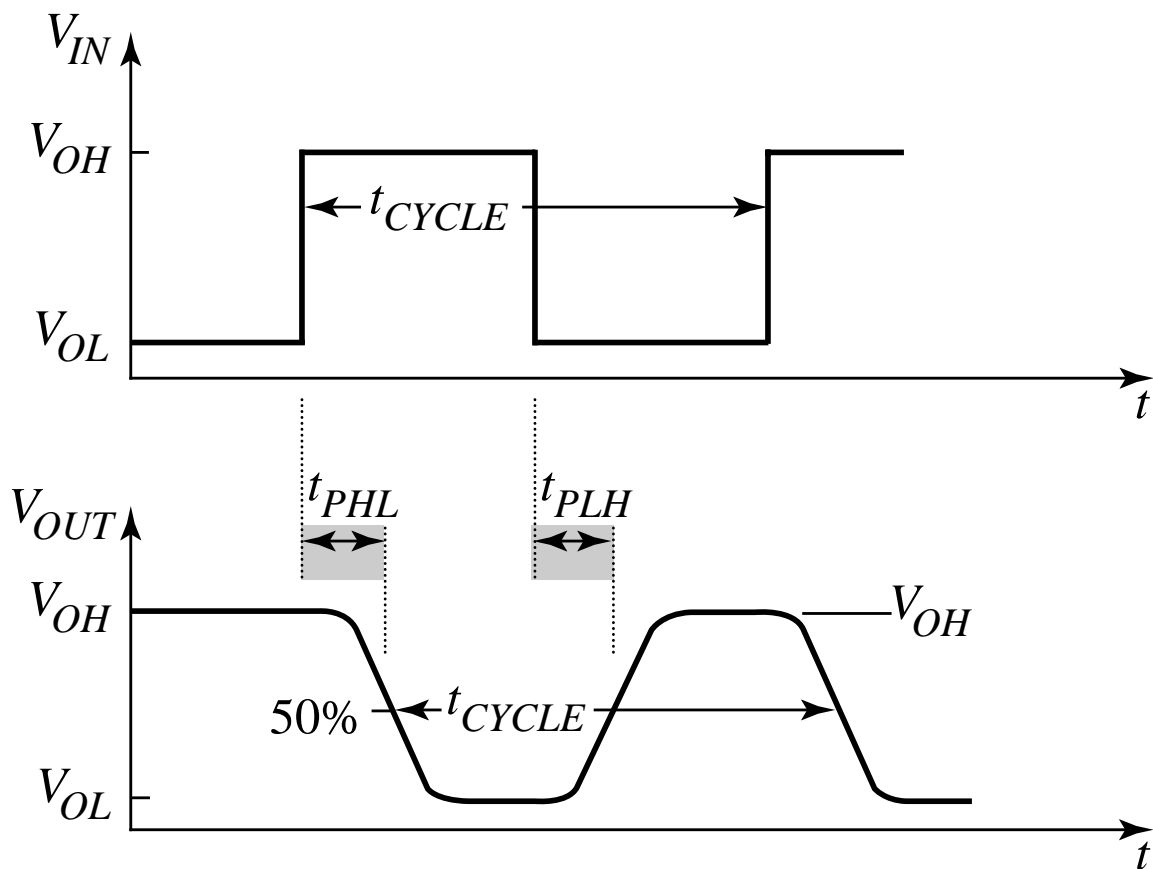
t_{PHL} \equiv *propagation delay from high-to-low* between 50% points

t_{PLH} \equiv *propagation delay from low-to-high* between 50% points

$$\text{Propagation delay : } t_P = \frac{1}{2} (t_{PHL} + t_{PLH})$$

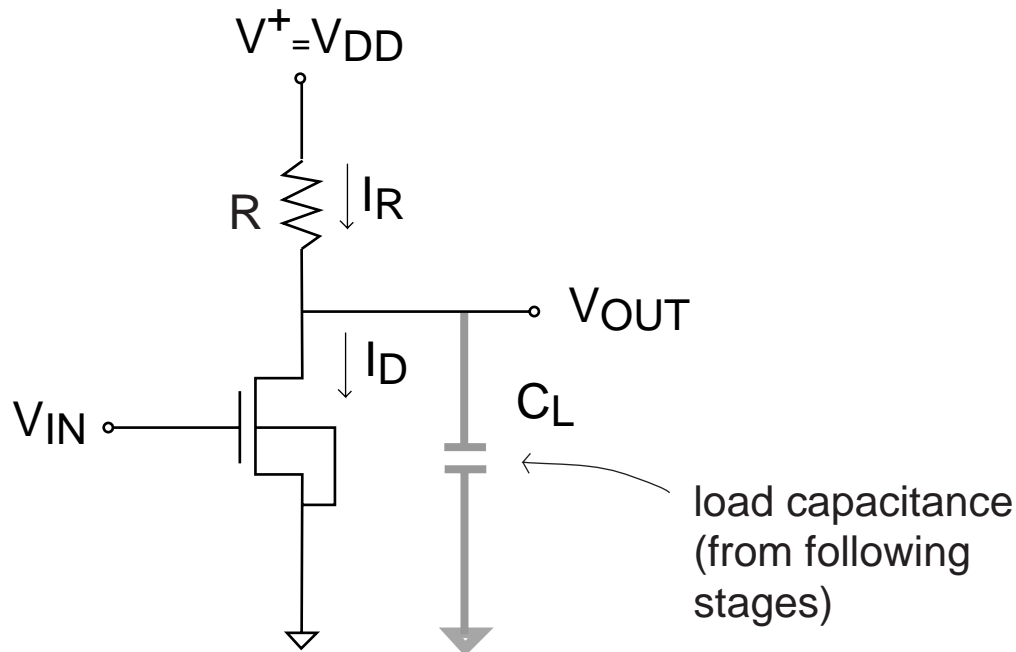
Simplifications for hand calculations: Propagation delay

- Consider input waveform is an ideal square wave
- Propagation delay times = delay times to 50% point



- **SPICE essential for accurate delay analysis**

2. NMOS inverter with “pull-up” resistor

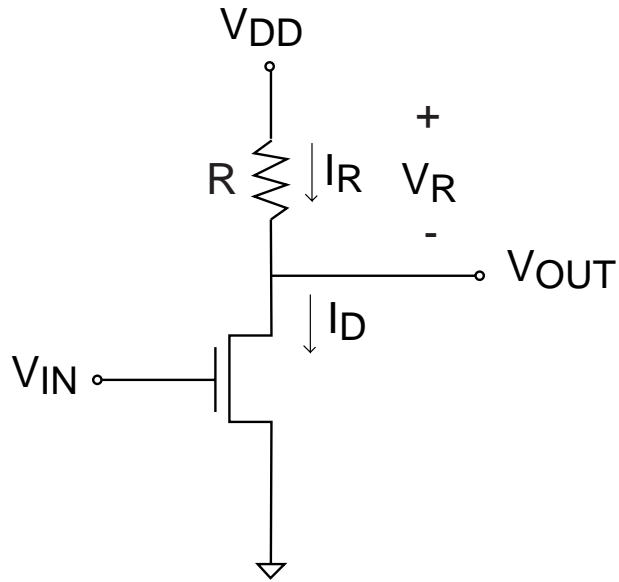


Essential features:

- $V_{BS} = 0$ (typically not shown)
- C_L summarizes capacitive loading of the following stages (other logic gates, interconnect lines, etc.)

Basic Operation:

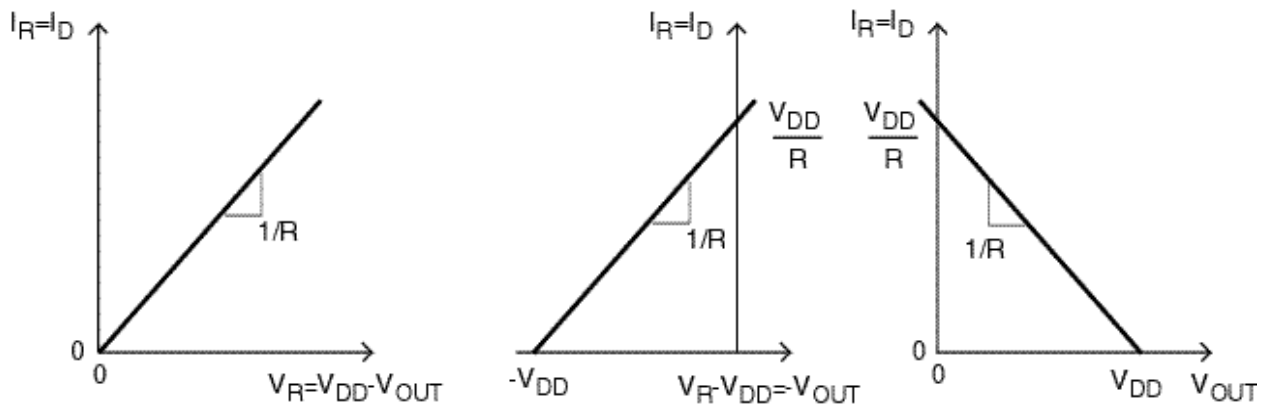
- If $V_{IN} < V_T$, MOSFET is **OFF**
 - $\Rightarrow V_{OUT} = V_{DD}$
- If $V_{IN} > V_T$, MOSFET is **ON**
 - $\Rightarrow V_{OUT}$ small
 - Value set by resistor / nMOS divider



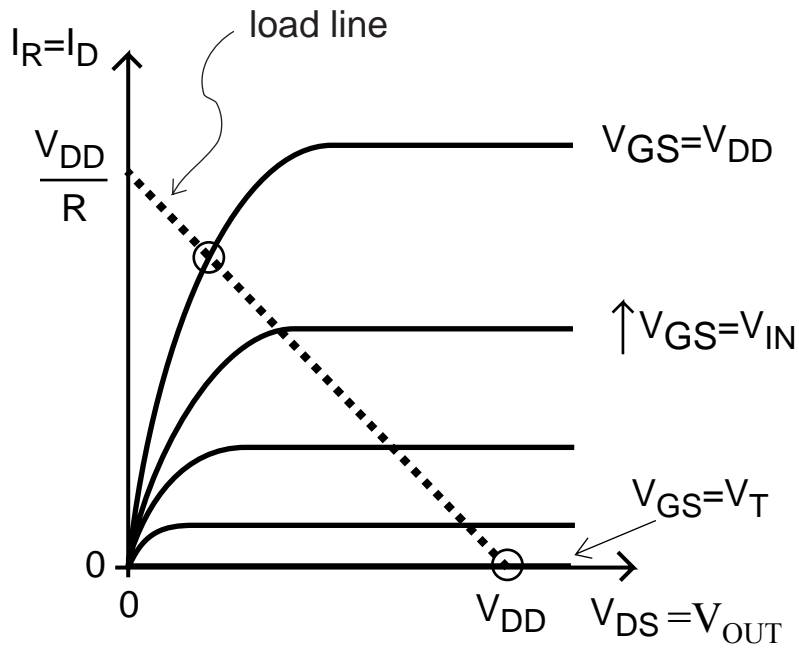
Transfer function obtained by solving:

$$I_R = I_D$$

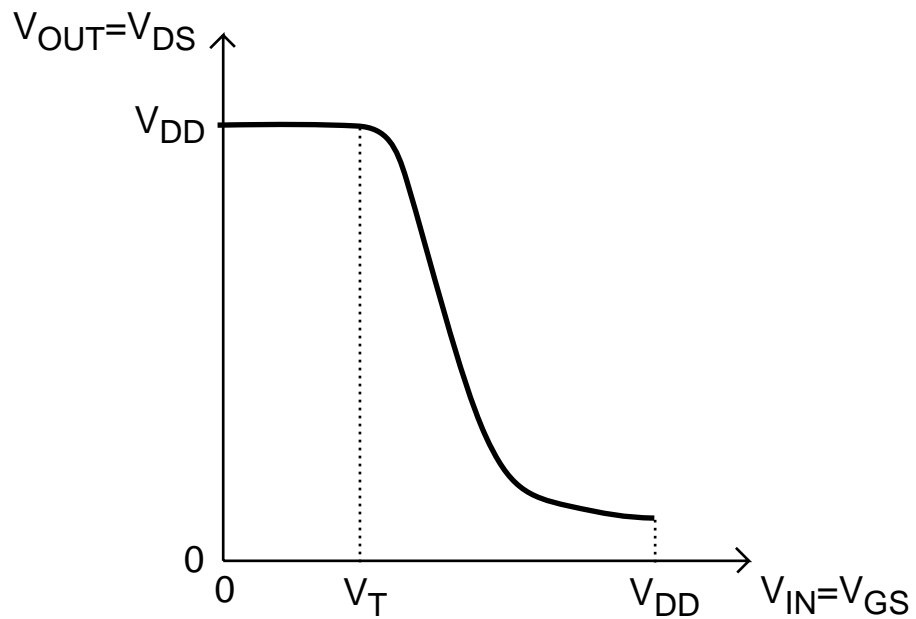
Can solve graphically: I–V characteristics of load:



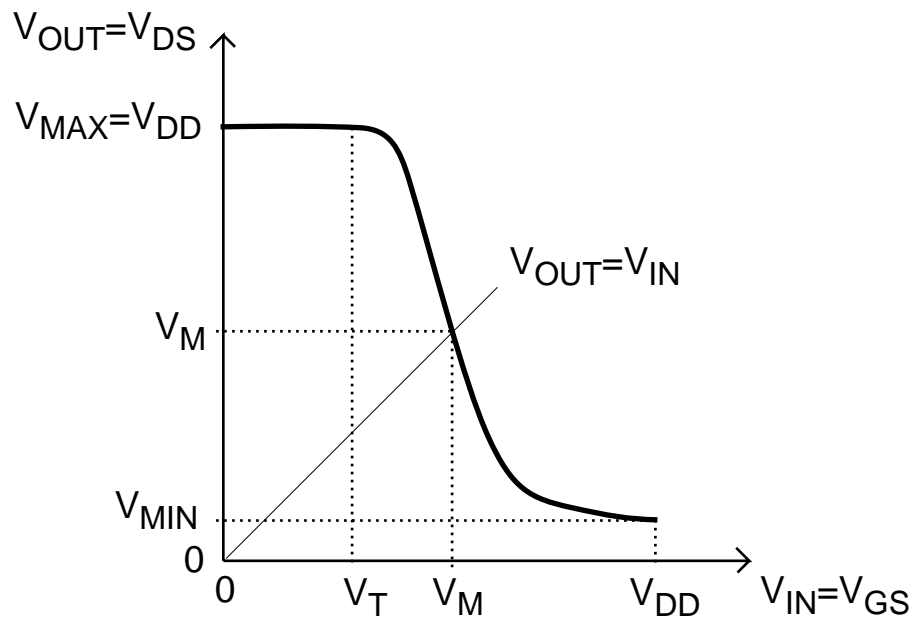
Overlap I–V characteristics of resistor pull-up on I–V characteristics of transistor:



Transfer function:



Logic levels:



For V_{MAX} , transistor is cut-off, $I_D = 0$:

$$V_{MAX} = V_{DD}$$

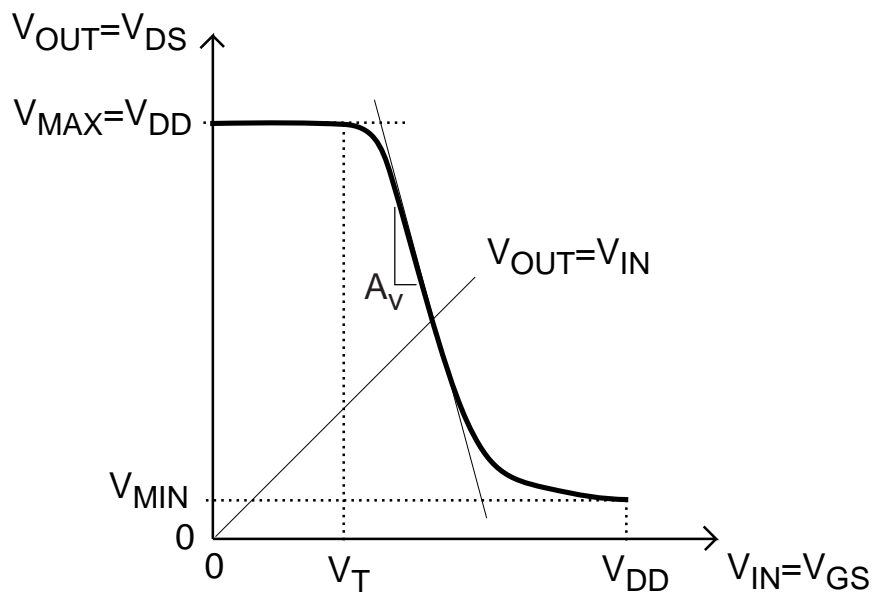
For V_{MIN} , transistor is in linear regime; solve:

$$I_D = \frac{W}{L} \mu_n C_{ox} \left(V_{DD} - \frac{V_{MIN}}{2} - V_T \right) V_{MIN} = I_R = \frac{V_{DD} - V_{MIN}}{R}$$

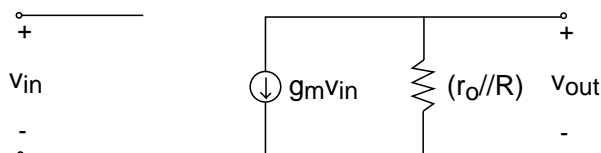
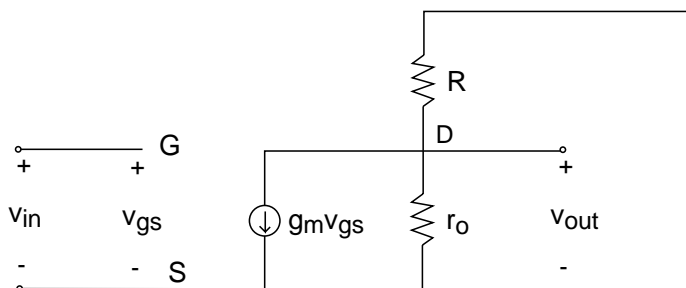
For V_M , transistor is in saturation; solve:

$$I_D = \frac{W}{2L} \mu_n C_{ox} (V_M - V_T)^2 = I_R = \frac{V_{DD} - V_M}{R}$$

Noise Margins:



Small signal equivalent circuit model at V_M
(transistor in saturation):



$$A_v = \frac{v_{out}}{v_{in}} = -g_m (r_o // R) \approx -g_m R$$

What did we learn today?

Summary of Key Concepts

- Logic circuits must exhibit immunity to noise in the input signal
 - *Noise margins*
- Logic circuits must be *regenerative*
 - Able to restore clean logic values even if input is noisy.
- *Propagation delay*: time for logic gate to perform its function.
- Concept of *load line*: graphical technique to visualize transfer characteristics of inverter.
- First-order solution (by hand) of inverter figures-of-merit easy if *regions of operation* of transistor are correctly identified.
- For more accurate solutions, use SPICE (or other CAD tool).